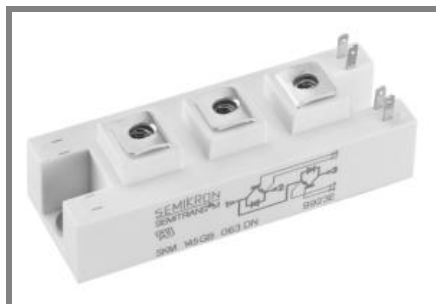




SEMITRANS® 2N

Ultra Fast IGBT Module

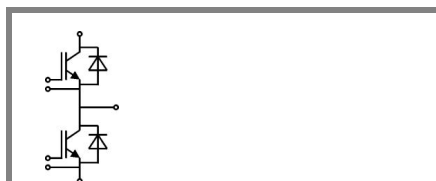
SKM 100GB125DN

Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications*

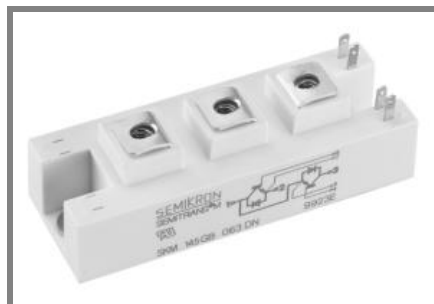
- Switched mode power supplies at $f_{sw} > 20$ kHz
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20$ kHz



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Absolute Maximum Ratings				$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25^\circ\text{C}$			1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$		100	A
		$T_{case} = 85^\circ\text{C}$		80	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$			150	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$			10	μs
Inverse Diode					
I_F	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$		95	A
		$T_{case} = 80^\circ\text{C}$		65	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			150	A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 150^\circ\text{C}$		720	A
Module					
$I_{t(RMS)}$				200	A
T_{vj}				- 40 ... + 150	$^\circ\text{C}$
T_{stg}				125	$^\circ\text{C}$
V_{isol}	AC, 1 min.			4000	V

Characteristics			T _c = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 2 mA		4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C T _j = 125 °C		0,15	0,45	mA mA
V _{CE0}		T _j = 25 °C T _j = 125 °C				V V
r _{CE}	V _{GE} = 15 V	T _j = 25°C T _j = 125°C				mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 75 A, V _{GE} = 15 V	T _j = °C _{chiplev.}		3,3	3,85	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		5	6,6	nF
C _{oes}				0,72	0,9	nF
C _{res}				0,38	0,5	nF
Q _G	V _{GE} = 0 - +20V			650		nC
R _{Gint}	T _j = °C			5		Ω
t _{d(on)}	R _{Gon} = 8 Ω	V _{CC} = 600V I _C = 75A T _j = 125 °C V _{GE} = ± 15V		80		ns
t _r				40		ns
E _{on}				9		mJ
t _{d(off)}	R _{Goff} = 8 Ω			360		ns
t _f				20		ns
E _{off}				3,5		mJ
R _{th(j-c)}	per IGBT				0,18	K/W



SEMITRANS® 2N

Ultra Fast IGBT Module

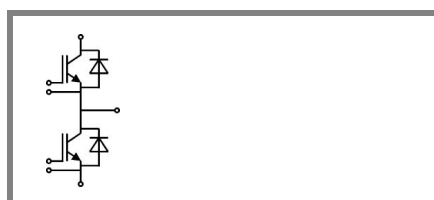
SKM 100GB125DN

Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{cnom}$
- Fast & soft inverse CAL diodes
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- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications*

- Switched mode power supplies at $f_{sw} > 20$ kHz
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20$ kHz



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Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 75$ A; $V_{GE} = 0$ V				
	$T_j = 25$ °C _{chiplev.}		2	2,5	V
	$T_j = 125$ °C _{chiplev.}		1,8		V
V_{F0}	$T_j = 25$ °C		1,1	1,2	V
	$T_j = 125$ °C				V
r_F	$T_j = 25$ °C		12	17,3	mΩ
	$T_j = 125$ °C				mΩ
I_{RRM}	$I_F = 75$ A		50		A
Q_{rr}	$di/dt = 800$ A/μs		11,5		μC
E_{rr}	$V_{GE} = 0$ V; $V_{CC} = 600$ V		4		mJ
$R_{th(j-c)D}$	per diode			0,5	K/W
Module					
L_{CE}			20	25	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25$ °C	0,75		mΩ
		$T_{case} = 125$ °C	1		mΩ
$R_{th(c-s)}$	per module			0,05	K/W
M_s	to heat sink M6		3	5	Nm
M_t	to terminals M5		2,5	5	Nm
w				160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.

SKM 100GB125DN



SEMITRANS® 2N

Ultra Fast IGBT Module

SKM 100GB125DN

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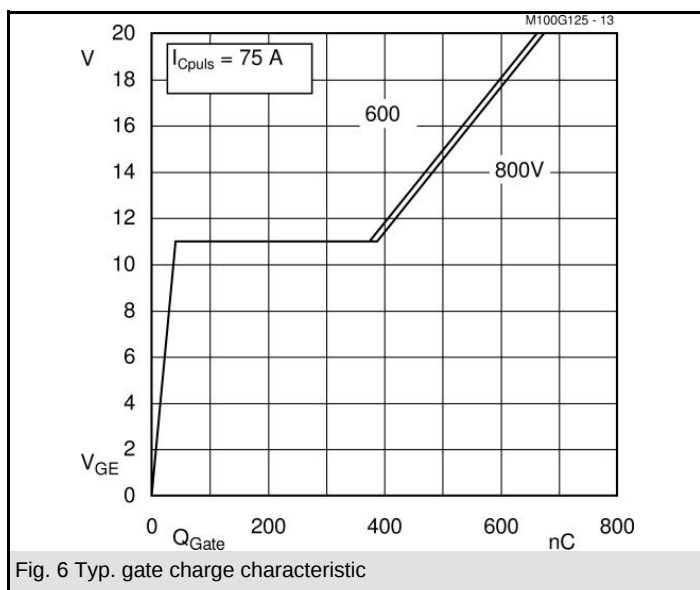
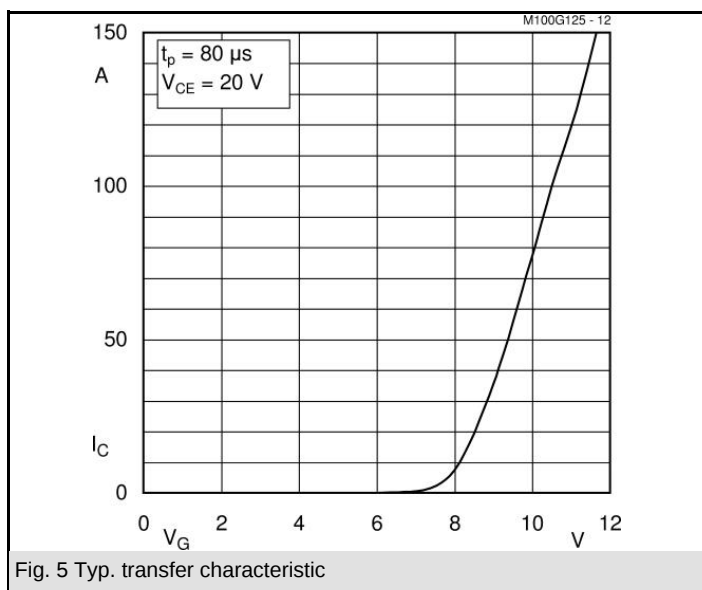
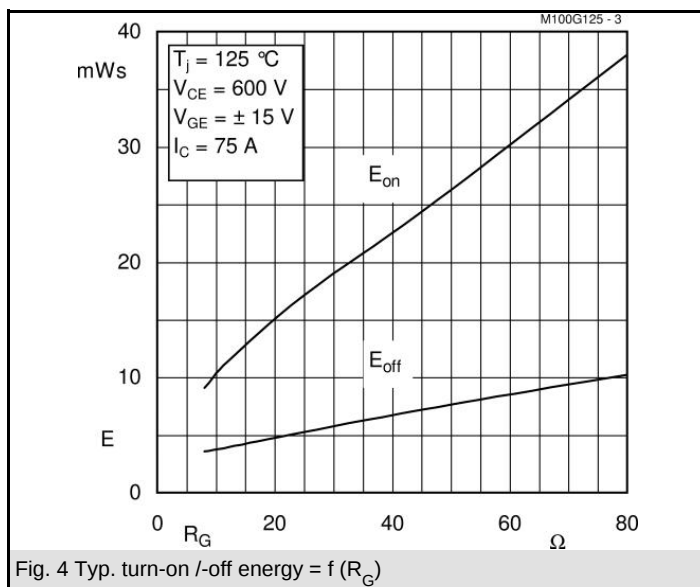
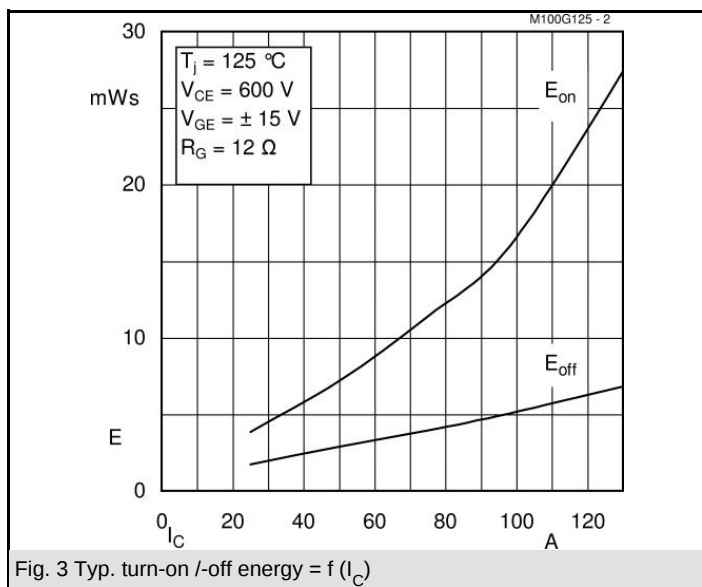
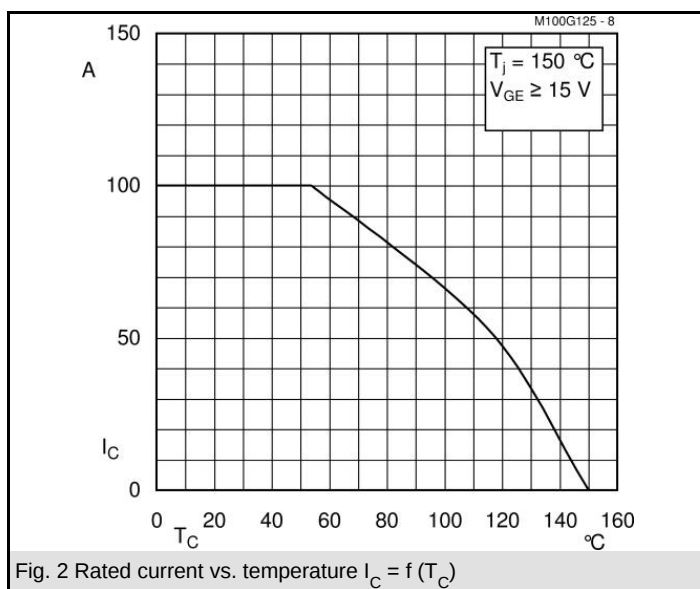
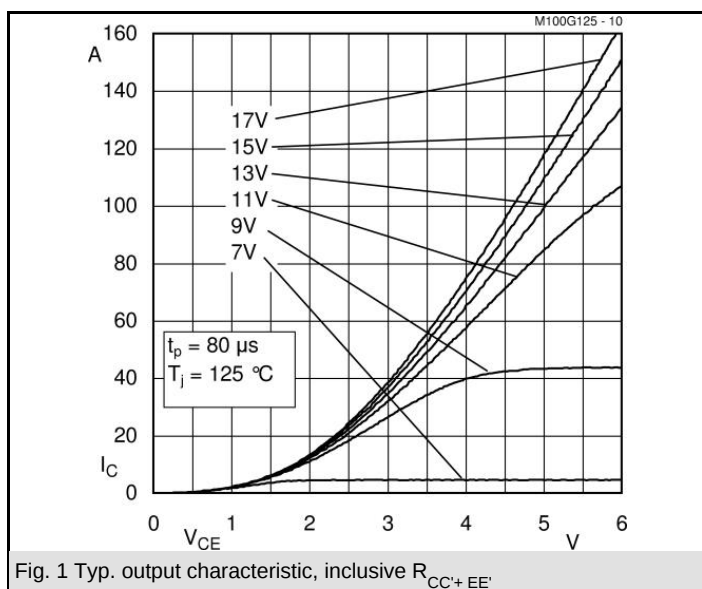
Typical Applications*

- Switched mode power supplies at $f_{sw} > 20\text{ kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$



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Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	95	mk/W
R_i	$i = 2$	65	mk/W
R_i	$i = 3$	17,5	mk/W
R_i	$i = 4$	2,5	mk/W
τ_{ui}	$i = 1$	0,0327	s
τ_{ui}	$i = 2$	0,008	s
τ_{ui}	$i = 3$	0,0017	s
τ_{ui}	$i = 4$	0,008	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	300	mk/W
R_i	$i = 2$	160	mk/W
R_i	$i = 3$	36	mk/W
R_i	$i = 4$	4	mk/W
τ_{ui}	$i = 1$	0,054	s
τ_{ui}	$i = 2$	0,001	s
τ_{ui}	$i = 3$	0,0015	s
τ_{ui}	$i = 4$	0,1	s



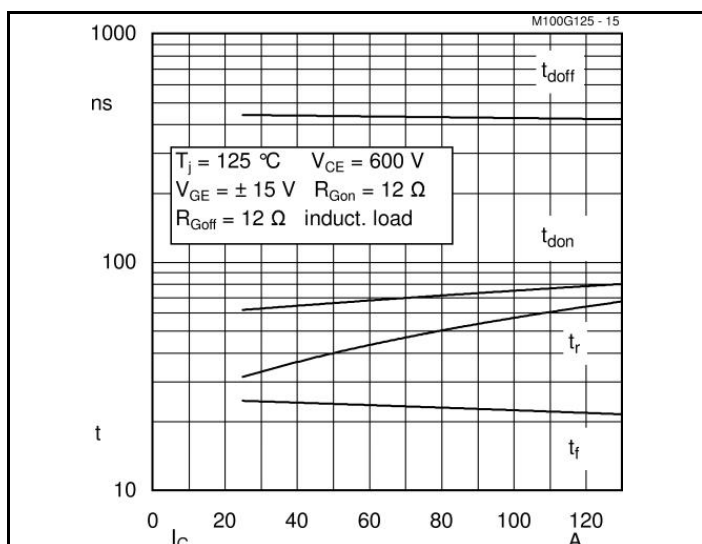


Fig. 7 Typ. switching times vs. I_C

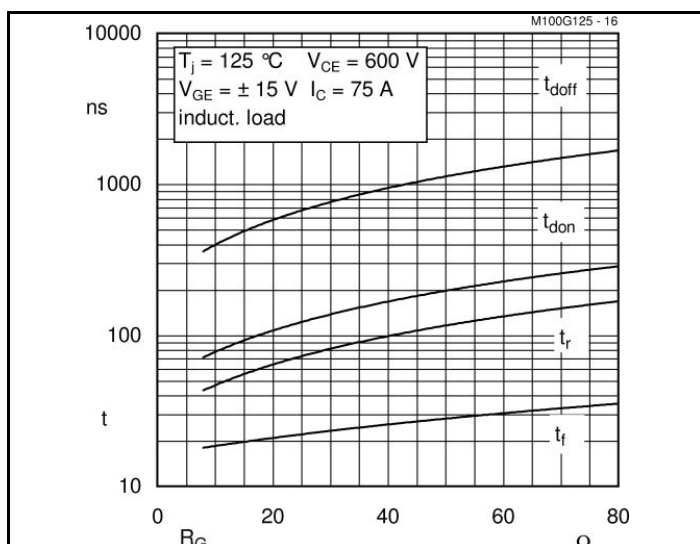


Fig. 8 Typ. switching times vs. gate resistor R_G

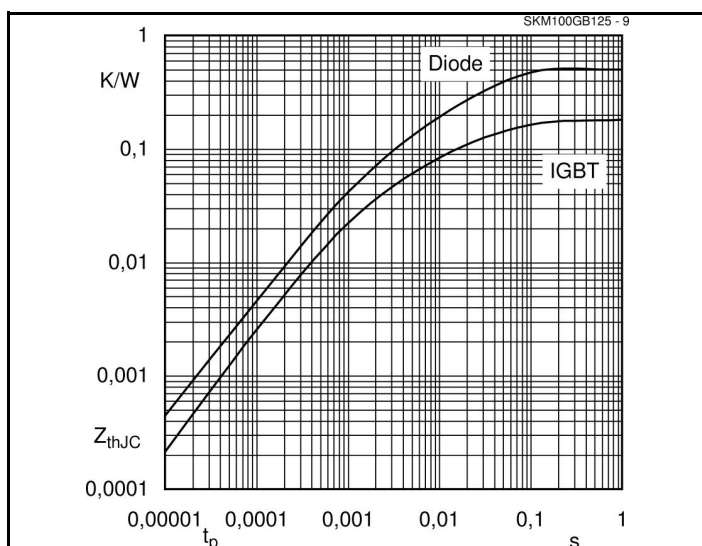


Fig. 9 Transient thermal impedance

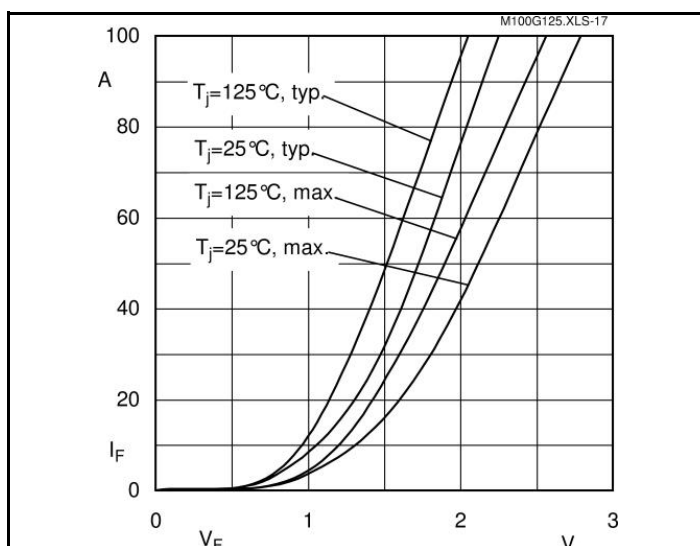


Fig. 10 CAL diode forward characteristic

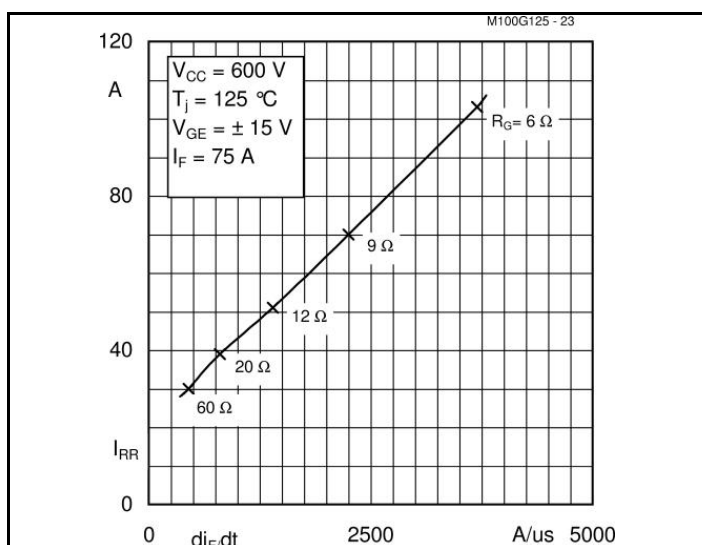


Fig. 11 Typ. CAL diode peak reverse recovery current

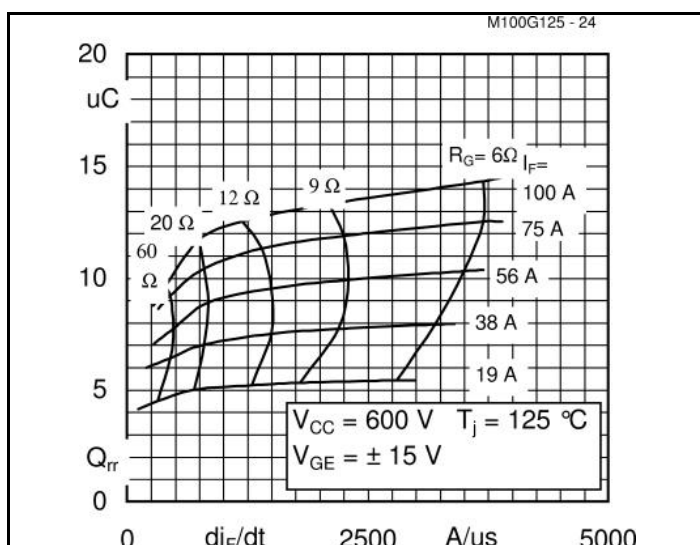
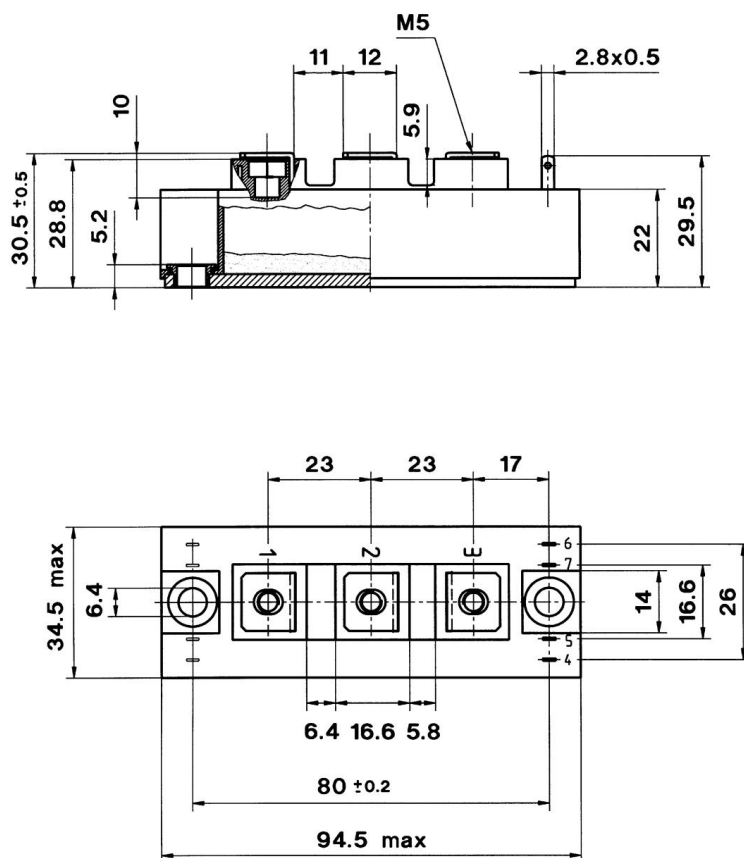
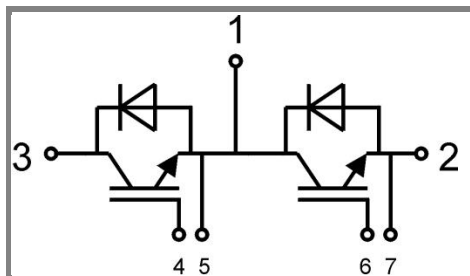


Fig. 12 Typ. CAL diode peak reverse recovery charge



CASED93

Case D 93



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Case D 93